

## 1024 BIT (256x4) STATIC CMOS RAM

#### DESCRIPTION

The µPD5.101L and µPD5.101L-1 are very low power 1024 bit (256 words by 4 bits) static CMOS Random Access Memories. They meet the low power requirements of battery operated systems and can be used to ensure non-volatility of data in systems using battery backup power.

All inputs and outputs of the  $\mu$ PD5101L and  $\mu$ PD5101L-1 are TTL compatible. Two chip enables  $(\overline{CE}_1, CE_2)$  are provided, with the devices being selected when  $\overline{CE}_1$  is low and CE2 is high. The devices can be placed in standby mode, drawing 10  $\mu$ A maximum, by driving  $\overline{CE}_1$  high and inhibiting all address and control line transitions. The standby mode can also be selected unconditionally by driving CE2 low.

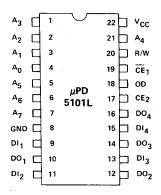
The µPD5101L and µPD5101L-1 have separate input and output lines. They can be used in common I/O bus systems through the use of the OD (Output Disable) pin and OR-tying the input/output pins. Output data is the same polarity as input data and is nondestructively read out. Read mode is selected by placing a high on the R/W pin. Either device is guaranteed to retain data with the power supply voltage as low as 2.0 volts. Normal operation requires a single +5 volt supply.

The µPD5101L and µPD5101L-1 are fabricated using NEC's silicon gate complementary MOS (CMOS) process.

#### **FEATURES**

- Directly TTL Compatible All Inputs and Outputs
- · Three-State Output
- Access Time 650 ns (μPD5101L); 450 ns (μPD5101L-1)
- Single +5V Power Supply
- CE<sub>2</sub> Controls Unconditional Standby Mode
- For operation at +3V Power Supply, Contact the NEC Sales Office.

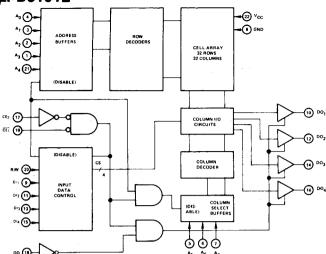
### PIN CONFIGURATION



#### **PIN NAMES**

DI1 - DI4	Data Input
A0 - A7	Address Inputs
R/W	Read/Write Input
CE <sub>1</sub> , CE <sub>2</sub>	Chip Enables
OD	Output Disable
DO <sub>1</sub> - DO <sub>4</sub>	Data Output
Vcc	Power (+5V)

# μPD5101L



**BLOCK DIAGRAM** 

Voltage On Any Pin With Respect to Ground . . . . -0.3 Volts to V<sub>CC</sub> +0.3 Volts Power Supply Voltage . . . . . . . . . . . . -0.3 to +7.0 Volts

 $T_a = 25^{\circ}C$ 

\*COMMENT: Stress above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

 $T_a = 0^{\circ}C$  to  $70^{\circ}C$ ;  $V_{CC} = +5V \pm 5\%$ , unless otherwise specified.

		LIMITS				
PARAMETER	SYMBOL	MIN	түр ①	MAX	UNIT	TEST CONDITIONS
Input High Leakage	'LIH@			1	μА	V <sub>IN</sub> = V <sub>CC</sub>
Input Low Leakage	1L1L@			- 1	μΑ	V <sub>IN</sub> = 0V
Output High Leakage	¹LOH②			1	μΑ	$\overline{CE}_1 = 2.2V, V_{OUT} = V_{CC}$
Output Low Leakage	ILOL ②			-1	μΑ	CE <sub>1</sub> = 2.2V, V <sub>OUT</sub> = 0.0V
Operating Current	I <sub>CC1</sub>			22	mA	V <sub>IN</sub> = V <sub>CC</sub> Except CE <sub>1</sub> ≤0.65V, Outputs Open
Operating Current	ICC2			27	mA	V <sub>IN</sub> = 2.2V Except CE <sub>1</sub> ≤0.65V, Outputs Open
Standby Current	'ccl2			10	μА	V <sub>IN</sub> = 0 to 5.25V CE <sub>2</sub> ≤ 0.2V
Input Low Voltage	VIL	-0.3		0.65	٧	
Input High Voltage	ViH	2.2		Vcc	>	
Output Low Voltage	VOL			0.4	>	I <sub>OL</sub> = 2.0 mA
Output High Voltage	V <sub>OH1</sub>	2.4			٧	I <sub>OH</sub> = -1.0 mA
Output High Voltage	V <sub>OH2</sub>	3.5			V	I <sub>OH</sub> = -100 μA

Notes: 1 Typical values at  $T_a = 25^{\circ}$ C and nominal supply voltage.

② Current through all inputs and outputs included in ICCL.

		LIMITS				
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Input Capacitance (All Input Pins)	CIN		4	8	pF	V <sub>IN</sub> - 0V
Output Capacitance	COUT		8	12	pF	V <sub>OUT</sub> - 0V

DC CHARACTERISTICS

ABSOLUTE MAXIMUM

**RATINGS\*** 

CAPACITANCE

 $T_a = 0^{\circ}C$  to  $70^{\circ}C$ ;  $V_{CC} = 5V\pm5\%$ , unless otherwise specified

		<b>I</b>		LIF	AITS				
PARAMETER	SYMBOL	5101L			5101L-1			UNIT	TEST CONDITIONS
		MIN	TYP	MAX	MIN	TYP	MAX		
Read Cycle	<sup>†</sup> RC	650			450			ns	Input pulse amplitude 0.65 to 2,2 Volts
Access Time	t <sub>A</sub>			650			450	ns	Input rise and fall
Chip Enable (CE <sub>1</sub> ) to Output	<sup>1</sup> CO1			600			400	กร	times: 20 ns
Chip Enable (CE <sub>2</sub> ) to Output	¹CO2			700			500	ns	Timing measurement reference level: 1,5 Volt
Output Disable to Output	dO <sup>‡</sup>			350			250	ns	Output load: ITTL
Deta Output to High Z State	¹DF	0		150	0		130	ns	Gate and C <sub>L</sub> ≈ 100 pf
Previous Read Data Valid with Respect to Address Change	tOH1	0			٥			ns	
Previous Read Data Valid with Respect to Chip Enable	<sup>t</sup> OH2	0			0			ηS	

#### WRITE CYCLE

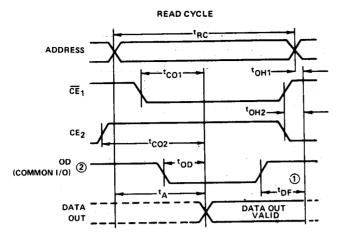
Ta = 0°C to 70°C; VCC = 5V±5%, unless otherwise specified

				LIM	IITS				1	
PARAMETER	SYMBOL	5101L			5101L-1			UNIT	TEST CONDITIONS	
		MIN	TYP	MAX	MIN	TYP	MAX			
Write Cycle	†WC	650			450			ns	Input pulse amplitude:	
Write Delay	<sup>t</sup> AW	150			130			ns	0,65 to 2,2 Volts	
Chip Enable (CE <sub>1</sub> ) to Write	<sup>1</sup> CW1	550			350			ns	Input rise and fall times: 20 ns	
Chip Enable (CE <sub>2</sub> ) to Write	tCW2	550			350			ns	Timing measurement reference level:	
Data Setup	†DW	400			250			ns	1,5 Volt	
Data Hold	tDH	100			50			ns	Output load: ITTL	
Write Pulse	†WP	400			250			ns	Gate and C <sub>L</sub> ≈	
Write Recovery	twR	50			50			ns	100 pF	
Output Disable Setup	tDS	150			130				1	

### LOW VCC DATA RETENTION Ta = 0°C to 70°C CHARACTERISTICS

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
V <sub>CC</sub> for Data Retention	VCCDR	+2.0			٧	CE <sub>2</sub> ≤ +0.2V
Data Retention Current	ICCDR			+10	μА	V <sub>CCDR</sub> = +2.0V CE <sub>2</sub> ≤ +0.2V
Chip Deselect Setup Time	†CDR	0			ns	
Chip Deselect Hold Time	tR	¹RCÛ			ns	

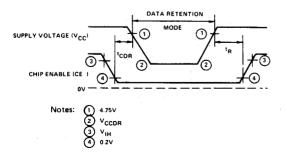
Note: 1 tRC = Read Cycle Time



# WRITE CYCLE twc ADDRESS t<sub>CW1</sub> CE<sub>1</sub> t<sub>CW2</sub> OD (COMMON 1/0)3 $^{\mathrm{t}}$ DH t<sub>DS</sub> DATA IN DATA t DW t<sub>WP</sub> R/W

Notes: ① Typical values are for T<sub>a</sub> = 25°C and nominal supply voltage. ② OD may be tied low for separate I/O operation. ③ During the write cycle, OD is "high" for common I/O and

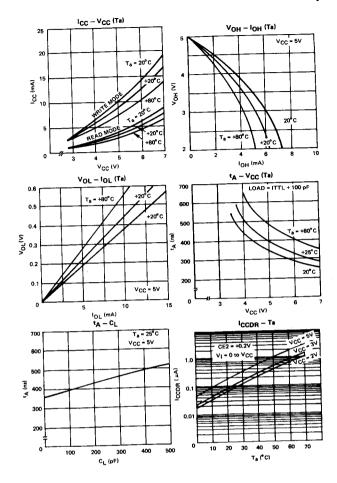
During the write cycle, OD is "high" for common I/O and "don't care" for separate I/O operation.



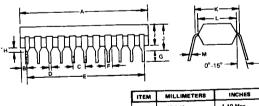
TIMING WAVEFORMS

LOW VCC DATA RETENTION

TYPICAL OPERATING CHARACTERISTICS







ITEM	MILLIMETERS	INCHES
Α	28.0 Max.	1,10 Max.
8	1,4 Max.	0.025 Max.
- c	2.54	0.10
D	0.50 0.10	0.02 0.004
Ē	25.4	1.0
F	1,40	0.055
G	2.54 Min.	0.10 Min.
H	0.5 Min.	0.02 Min.
	4,7 Max.	0.18 Max.
_;_	5.2 Max.	0.20 Max.
K	10.16	0.40
	8.5	0.33
м	0.25 <sup>+0.10</sup> 0.05	0.01 +0.004

5101LDS-REV1-12-81-CAT